

MITSUBISHI INSULATED GATE BIPOLAR TRANSISTOR

查询CT60AM20供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

CT60AM-20

RESONANT INVERTER USE

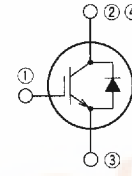
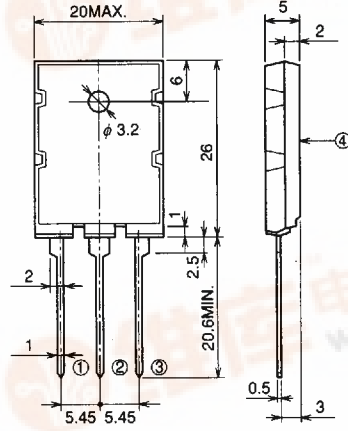
CT60AM-20



- VCES ..... 1000V
- IC ..... 60A
- Integrated Fast Recovery Diode

OUTLINE DRAWING

Dimensions in mm



- ① GATE
- ② COLLECTOR
- ③ EMITTER
- ④ COLLECTOR

TO-3PL

APPLICATION

Microwave ovens, electromagnetic cooking devices, rice-cookers, voltage-resonant inverter circuit electric appliances.

MAXIMUM RATINGS (Tc = 25°C)

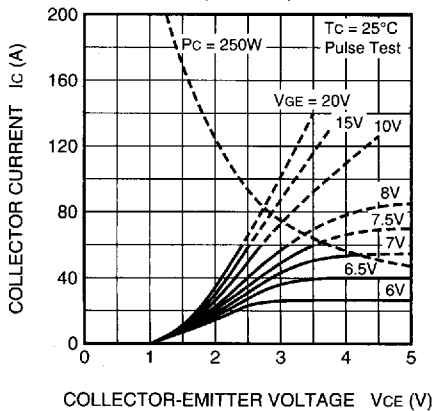
Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CE</sub> S	Collector-emitter voltage	V <sub>GE</sub> = 0V	1000	V
V <sub>GE</sub> S	Gate-emitter voltage	V <sub>CE</sub> = 0V	±20	V
V <sub>GEM</sub>	Peak gate-emitter voltage	V <sub>CE</sub> = 0V, t <sub>w</sub> = 0.5s	±30	V
I <sub>C</sub>	Collector current		60	A
I <sub>CM</sub>	Collector current (Pulsed)	t <sub>w</sub> = 1ms	120	A
I <sub>E</sub>	Emitter current		40	A
P <sub>tot</sub>	Maximum power dissipation	T <sub>C</sub> = 25°C	250	W
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +150	°C

**ELECTRICAL CHARACTERISTICS** (Tj = 25°C unless otherwise noted)

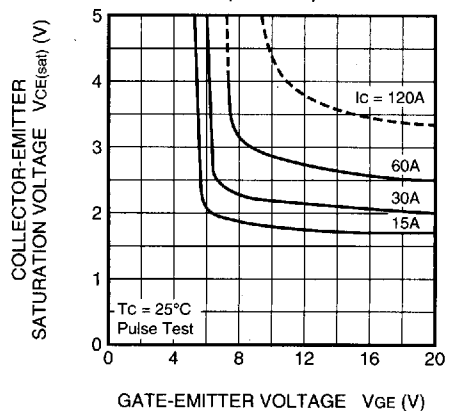
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector current	VCE = 1000V, VGE = 0V	—	—	1	mA
IGES	Gate leakage current	VGE = ±20V, VCE = 0V	—	—	±0.5	μA
VGE(th)	Gate-emitter threshold voltage	VCE = 10V, IC = 6mA	2.0	—	6.0	V
VCE(sat)	Collector-emitter saturation voltage	IC = 60A, VCE = 15V	—	2.6	3.5	V
Cies	Input capacitance	VCE = 25V, VGE = 0V, f = 1MHz	—	1950	—	pF
Coes	Output capacitance		—	170	—	pF
Cres	Reverse transfer capacitance		—	65	—	pF
td (on)	Turn-on delay time		—	0.04	—	μs
tr	Fall time	IC = 60A, Resistance load	—	0.15	—	μs
td (off)	Turn-off delay time	VCC = 300V, VGE = 15V, RG = 25Ω	—	0.30	—	μs
tr	Rise time	—	—	0.30	—	μs
Etail	Tail loss	ICP = 60A, Tj = 125°C, dv/dt = 200V/μs	—	0.6	1.0	mJ/pls
ICtail	Collector tail current	—	—	6	12	A
VEC	Emitter-collector voltage	IE = 60A	—	—	3	V
Trr	Reverse recovery time	IE = 60A, di/dt = 20A/μs	—	0.5	2	μs
Rth (j-c)	Thermal resistance (IGBT part)	Junction to case	—	—	0.5	°C/W
Rth (j-c)	Thermal resistance	Junction to case	—	—	4.0	°C/W

**PERFORMANCE CURVES**

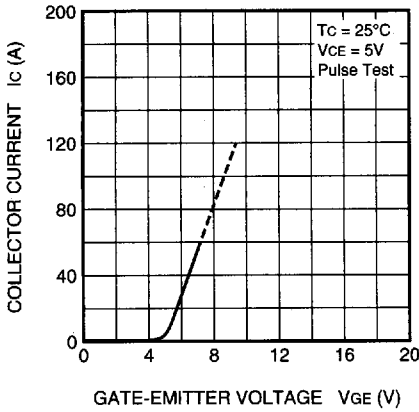
**OUTPUT CHARACTERISTICS (TYPICAL)**



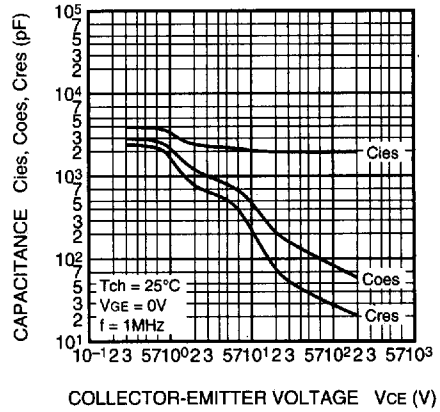
**COLLECTOR-EMITTER SATURATION VOLTAGE VS. GATE-EMITTER VOLTAGE (TYPICAL)**



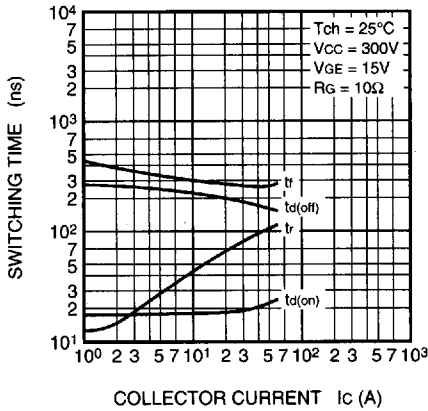
COLLECTOR CURRENT VS. GATE-EMITTER VOLTAGE (TYPICAL)



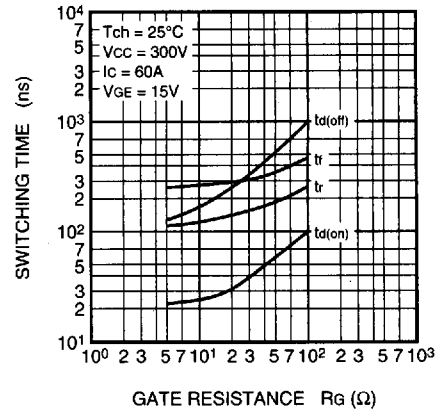
CAPACITANCE VS. COLLECTOR-EMITTER VOLTAGE (TYPICAL)



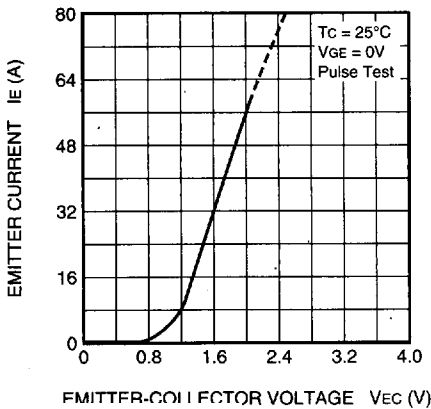
SWITCHING CHARACTERISTICS (TYPICAL)



SWITCHING TIME VS. GATE RESISTANCE (TYPICAL)



TRANSFER CHARACTERISTICS (TYPICAL)



# MITSUBISHI POWER MOSFET LEAD FORMING OUTLINE AND TAPING

## LEAD FORMING

(1) TO-220 outline

Applicable device FS\*\*UM-\*\*\*A

Standard outline	Standard forming outline				
	A5	A6	A8	AA	
Dimensions	$a=3.0\pm 0.5$ , $b=14.7\pm 0.5$ , $c=5.0\pm 0.5$ , $d=4.5\pm 0.5$ , $e=20.1\pm 0.5$ , $f=3.0\pm 0.5$ , $g=15.5\pm 0.5$ $h=16.0\pm 0.5$ , $i=5.5\pm 0.5$ ※Dimensions measured during processing				Unit : mm

(1) TO-220 full molded outline

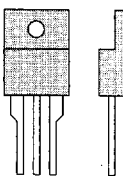
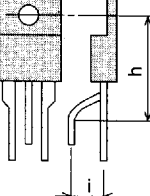
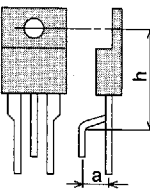
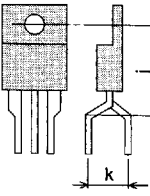
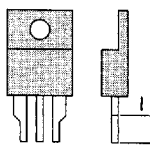
Applicable device FS\*\*KM-\*\*\*A

Standard outline	Standard forming outline				
	A5	A6	A8	AA	
Dimensions	$a=3.0\pm 0.5$ , $b=14.7\pm 0.5$ , $c=5.0\pm 0.5$ , $d=4.5\pm 0.5$ , $e=20.1\pm 0.5$ , $g=15.5\pm 0.5$ , $h=16.0\pm 0.5$ , $i=5.5\pm 0.5$ , $j=19.0\pm 0.5$ , $k=7.75\pm 0.5$ , $l=4.0\pm 0.5$ , $m=15.1\pm 0.5$ , $n=16.5\pm 0.5$ , $o=3.8\pm 0.35$ ※Dimensions measured during processing				Unit : mm

# MITSUBISHI POWER MOSFET LEAD FORMING OUTLINE AND TAPING

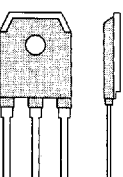
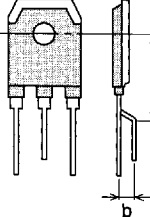
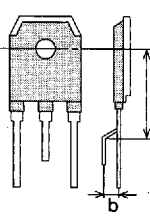
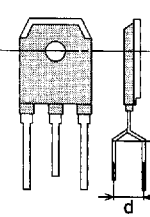
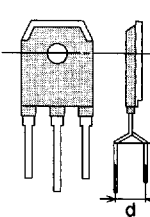
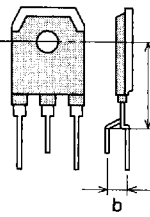
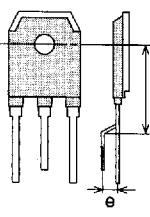
## (2) TO-220 full molded outline

Applicable device FS\*\*KM-\*\*\*A

Standard outline	Standard forming outline				
	AT	AU	AV	AW	
					
<b>Dimensions</b>	$a=3.0\pm 0.5, b=14.7\pm 0.5, c=5.0\pm 0.5, d=4.5\pm 0.5, e=20.1\pm 0.5, g=15.5\pm 0.5, h=16.0\pm 0.5,$ $i=5.5\pm 0.5, j=19.0\pm 0.5, k=7.75\pm 0.5, l=4.0\pm 0.5, m=15.1\pm 0.5, n=16.5\pm 0.5, o=3.8\pm 0.35$ ※Dimensions measured during processing				Unit : mm

## (3) TO-3P outline

Applicable device FS\*\*SM-\*\*\*A·CT\*\*SM-\*\*\*

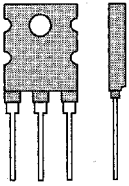
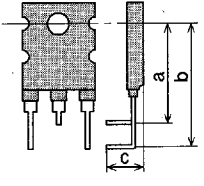
Standard outline	Standard forming outline				
	A7	A8	A9	AB	
					
					
<b>Dimensions</b>	$a=23.5, b=5.45, c=23, d=9.5, e=4, f=21.5$ ※Dimensions measured during processing				Unit : mm

MITSUBISHI POWER MOSFET

# LEAD FORMING OUTLINE AND TAPING

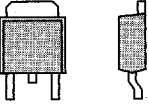
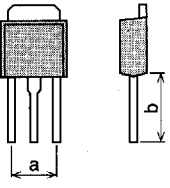
(4) TO-3PL outline

Applicable device CT\*\*AM-\*\*\*

Standard outline	Standard forming outline AC	Dimensions	
			<p> <math>a=24\pm0.5</math>  <math>b=31.5\pm0.5</math>  <math>c=13.3\pm0.6</math> </p> <p>※Dimensions measured during processing</p>

(5) MP-3 outline

Applicable device FS\*\*AS-\*\*A·CT20A\*\*8

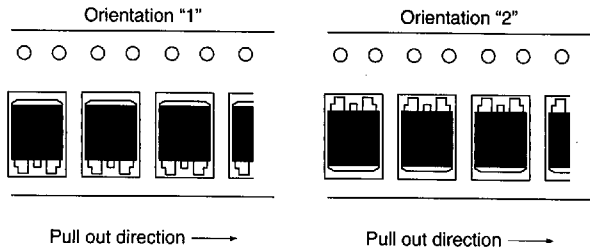
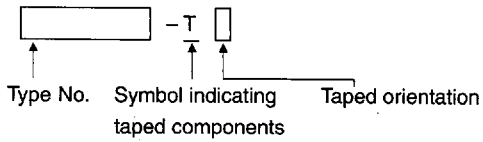
Standard outline	Standard forming outline A1	Dimensions	
			<p> <math>a=4.6</math>  <math>b=14\text{min.}</math> </p> <p>※Dimensions measured during processing</p>

# MITSUBISHI POWER MOSFET LEAD FORMING OUTLINE AND TAPING

## TAPING

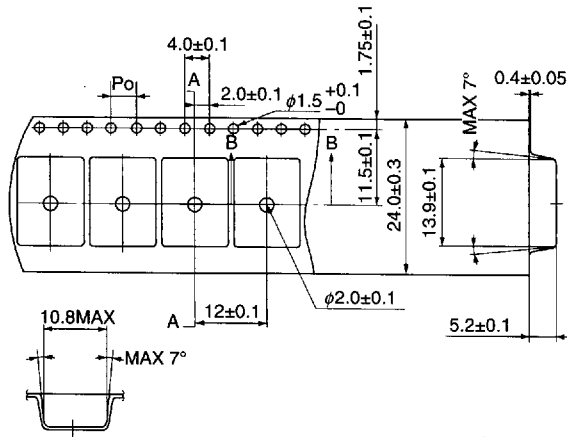
### (1) TO-220S

#### (a) Marking



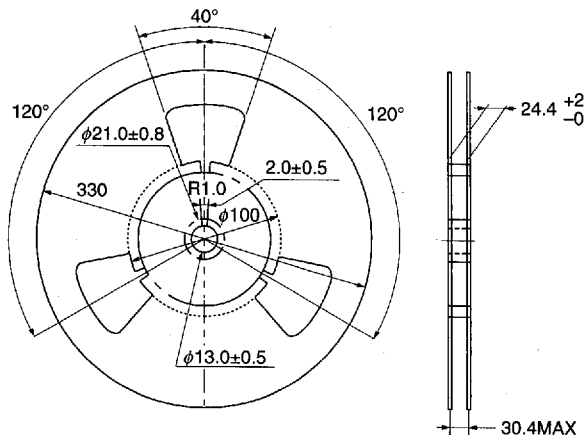
#### (b) Taping

##### • Tape shape and dimensions



Notice : The cumulative pitch error of  $P_o$  (Free hole pitch) is  $\pm 0.2\text{mm}$  per 10 pitches.

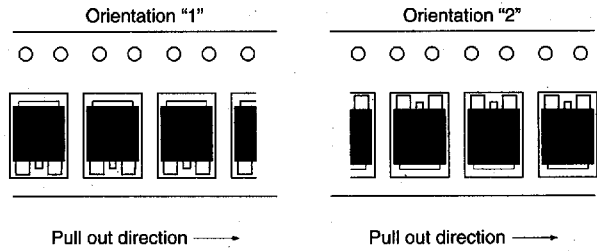
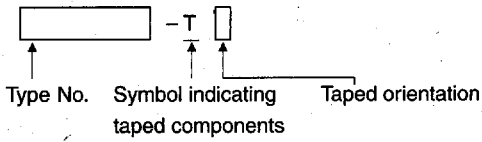
##### • Reel shape and dimensions



# MITSUBISHI POWER MOSFET LEAD FORMING OUTLINE AND TAPING

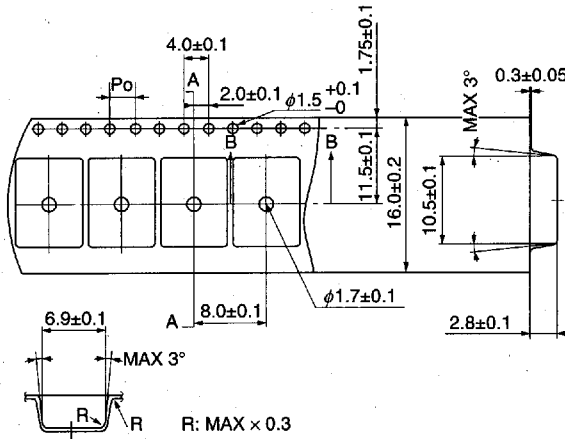
## (2) MP-3

### (a) Marking



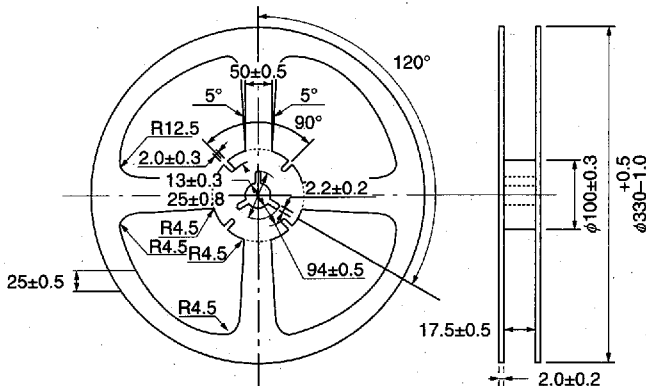
### (b) Taping

- Tape shape and dimensions



Notice : The cumulative pitch error of  $P_0$  (Free hole pitch) is  $\pm 0.2\text{mm}$  per 10 pitches.

- Reel shape and dimensions



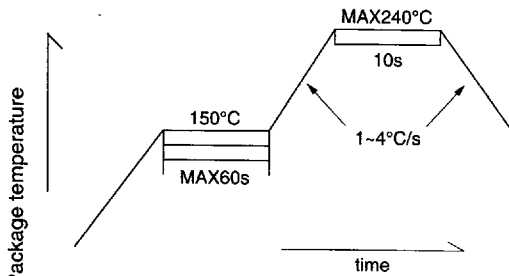


MITSUBISHI POWER MOSFET  
**LEAD FORMING OUTLINE AND TAPING**

**Recommended conditions for surface mounting type**

**Outline : TO-220S, MP-3**

- (1) Board : Alumina, Insulated metal board
- (2) Solder plate thickness : 150 $\mu$ m~250 $\mu$ m
- (3) Temperature profile

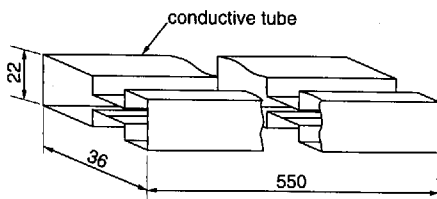


Infrared rays reflow temperature profile

**Individual package for lead forming outline**

- (1) TO-220, TO-220FN, TO-220C, TO-220S

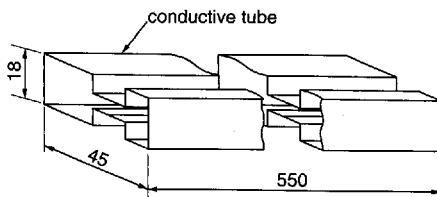
Dimensions in (Unit : mm)



The capacity is 50 p.c.s. (max.)

- (2) TO-3P

Dimensions in (Unit : mm)



The capacity is 30 p.c.s. (max.)

